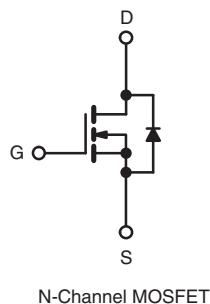


Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	400	
R _{DS(on)} (Ω)	V _{GS} = 10 V	1.0
Q _g (Max.) (nC)		38
Q _{gs} (nC)		5.7
Q _{gd} (nC)		22
Configuration		Single



ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHF730S-GE3	SiHF730STR-GE3 ^a	SiHF730STRR-GE3 ^a
Lead (Pb)-free	IRF730SPbF	IRF730STRLPbF ^a	-
	SiHF730S-E3	SiHF730STL-E3 ^a	-
	SiHF730S-E3	SiHF730STL-E3 ^a	-

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	400	
Gate-Source Voltage	V _{GS}	± 20	V
Continuous Drain Current	I _D	5.5 3.5	A
Pulsed Drain Current ^a	I _{DM}	22	
Linear Derating Factor		0.59 0.025	W/°C
Linear Derating Factor (PCB Mount) ^e			
Single Pulse Avalanche Energy ^b	E _{AS}	290	mJ
Avalanche Current ^a	I _{AR}	5.5	A
Repetitive Avalanche Energy ^a	E _{AR}	7.4	mJ
Maximum Power Dissipation	P _D	74 3.1	W
Maximum Power Dissipation (PCB Mount) ^e	T _A = 25 °C		
Peak Diode Recovery dV/dt ^c	dV/dt	4.0	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. V_{DD} = 50 V, starting T_J = 25 °C, L = 16 mH, R_g = 25 Ω, I_{AS} = 5.5 A (see fig. 12).
- c. I_{SD} ≤ 5.5 A, dI/dt ≤ 90 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- d. 1.6 mm from case.
- e. When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply



RoHS*
COMPLIANT
HALOGEN
FREE
Available

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	$^{\circ}\text{C}/\text{W}$
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

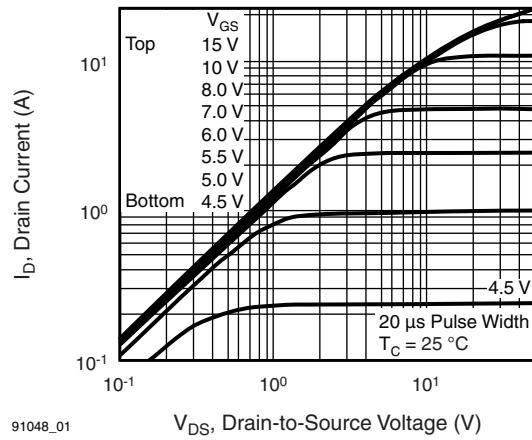
SPECIFICATIONS ($T_J = 25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$	$I_D = 250 \mu\text{A}$	400	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.54	-	$^{\circ}\text{C}/\text{V}$	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2.0	-	4.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 400 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	25	μA	
		$V_{DS} = 320 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^{\circ}\text{C}$		-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 3.3 \text{ A}^b$	-	-	1.0	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50 \text{ V}$, $I_D = 3.3 \text{ A}^b$		2.9	-	-	S	
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5		-	700	-	pF	
Output Capacitance	C_{oss}			-	170	-		
Reverse Transfer Capacitance	C_{rss}			-	64	-		
Total Gate Charge	Q_g	$V_{GS} = 10 \text{ V}$	$I_D = 3.5 \text{ A}$, $V_{DS} = 320 \text{ V}$, see fig. 6 and 13 ^b	-	-	38	nC	
Gate-Source Charge	Q_{gs}			-	-	5.7		
Gate-Drain Charge	Q_{gd}			-	-	22		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200 \text{ V}$, $I_D = 3.5 \text{ A}$, $R_g = 12 \Omega$, $R_D = 57 \Omega$, see fig. 10 ^b		-	10	-	ns	
Rise Time	t_r			-	15	-		
Turn-Off Delay Time	$t_{d(off)}$			-	38	-		
Fall Time	t_f			-	14	-		
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH	
Internal Source Inductance	L_S			-	7.5	-		
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	5.5	A	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	22		
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_S = 5.5 \text{ A}$, $V_{GS} = 0 \text{ V}^b$		-	-	1.6	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}$, $I_F = 3.5 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}^b$		-	270	530	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	1.8	2.2	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)						

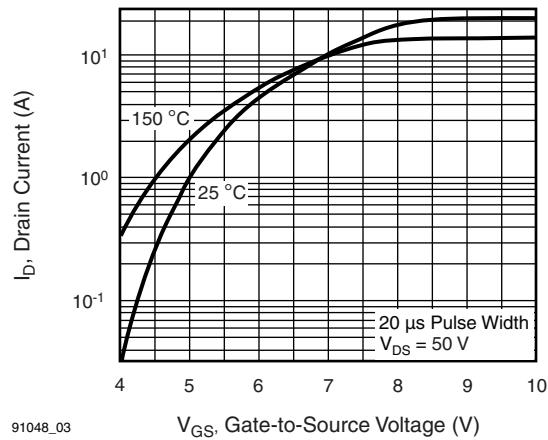
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


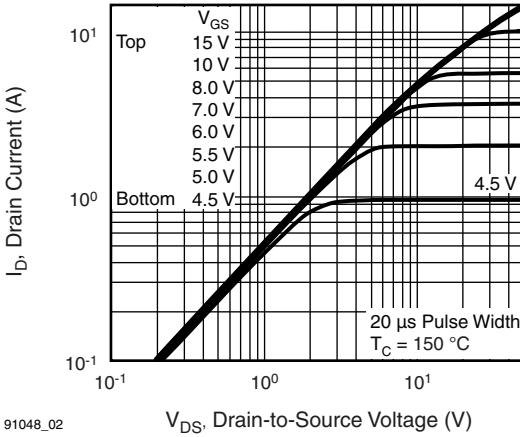
91048_01



91048_03

Fig. 1 - Typical Output Characteristics, $T_C = 25 \text{ }^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics



91048_02

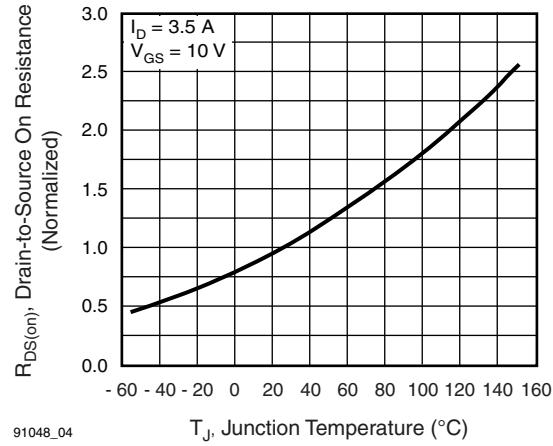


Fig. 4 - Normalized On-Resistance vs. Temperature

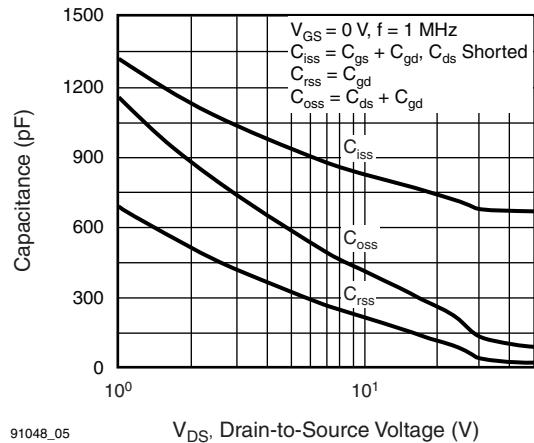


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

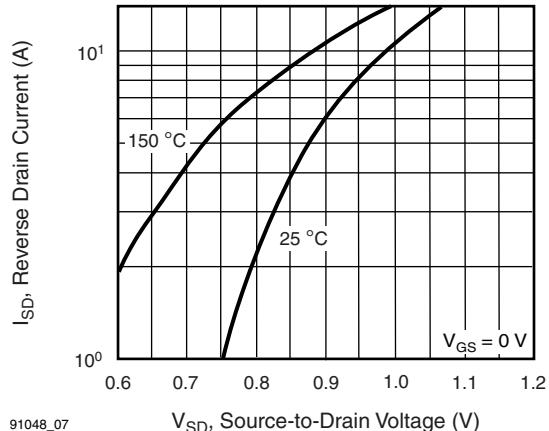


Fig. 7 - Typical Source-Drain Diode Forward Voltage

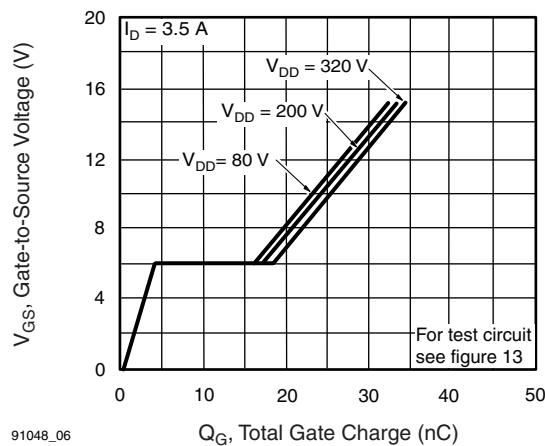


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

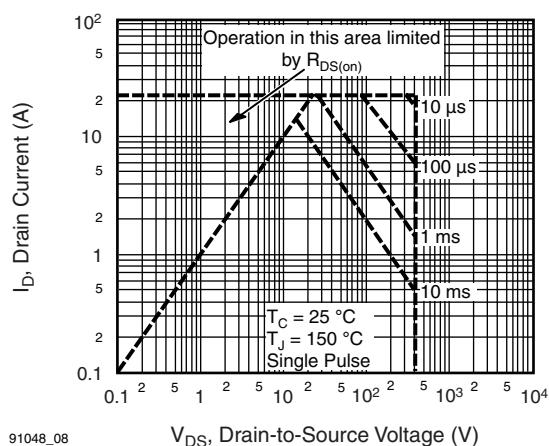
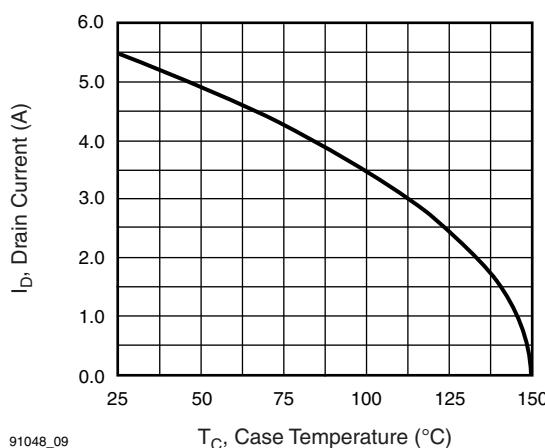
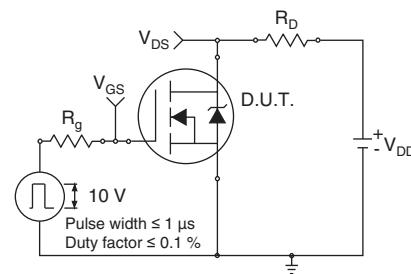
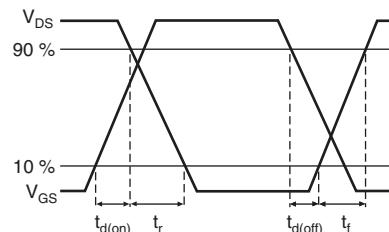
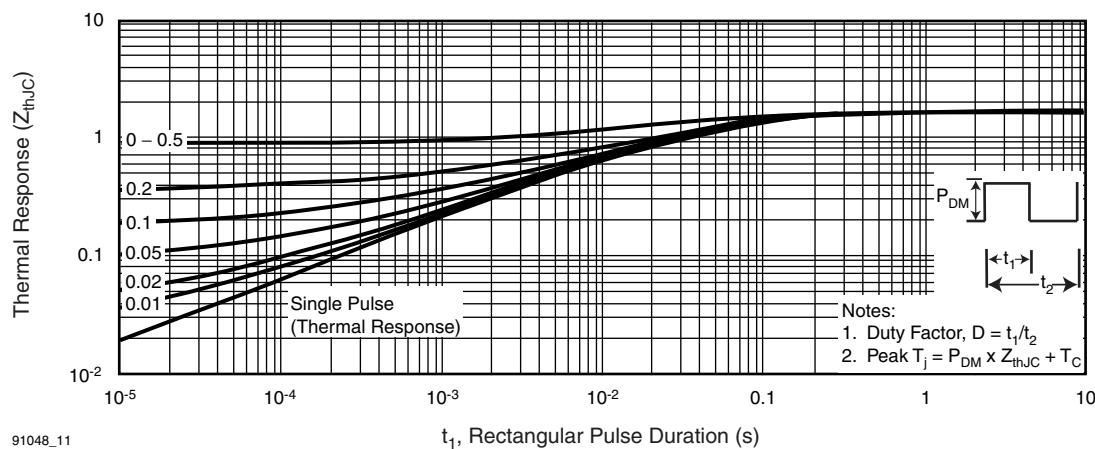


Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

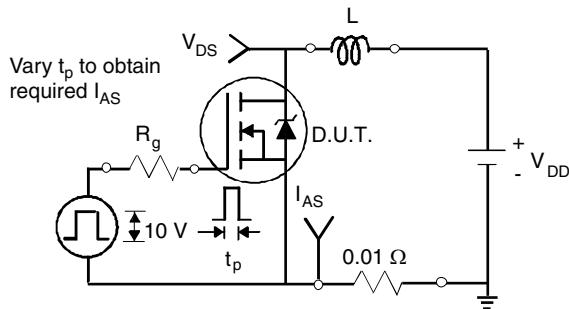


Fig. 12a - Unclamped Inductive Test Circuit

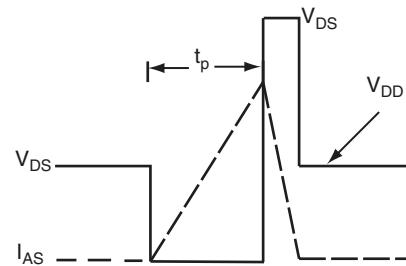


Fig. 12b - Unclamped Inductive Waveforms

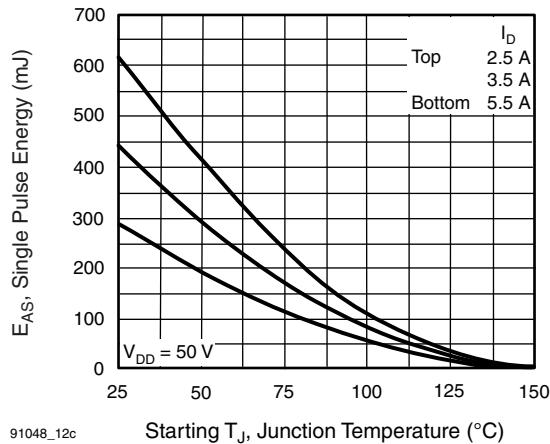


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

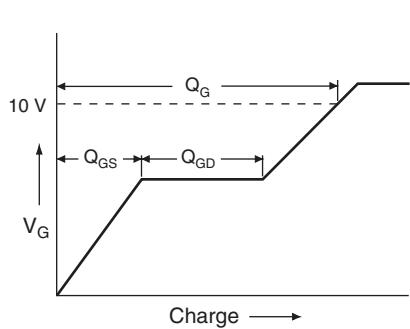


Fig. 13a - Basic Gate Charge Waveform

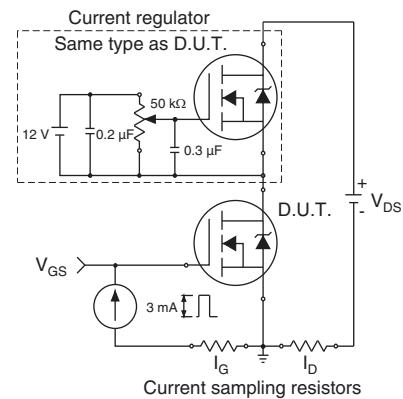


Fig. 13b - Gate Charge Test Circuit

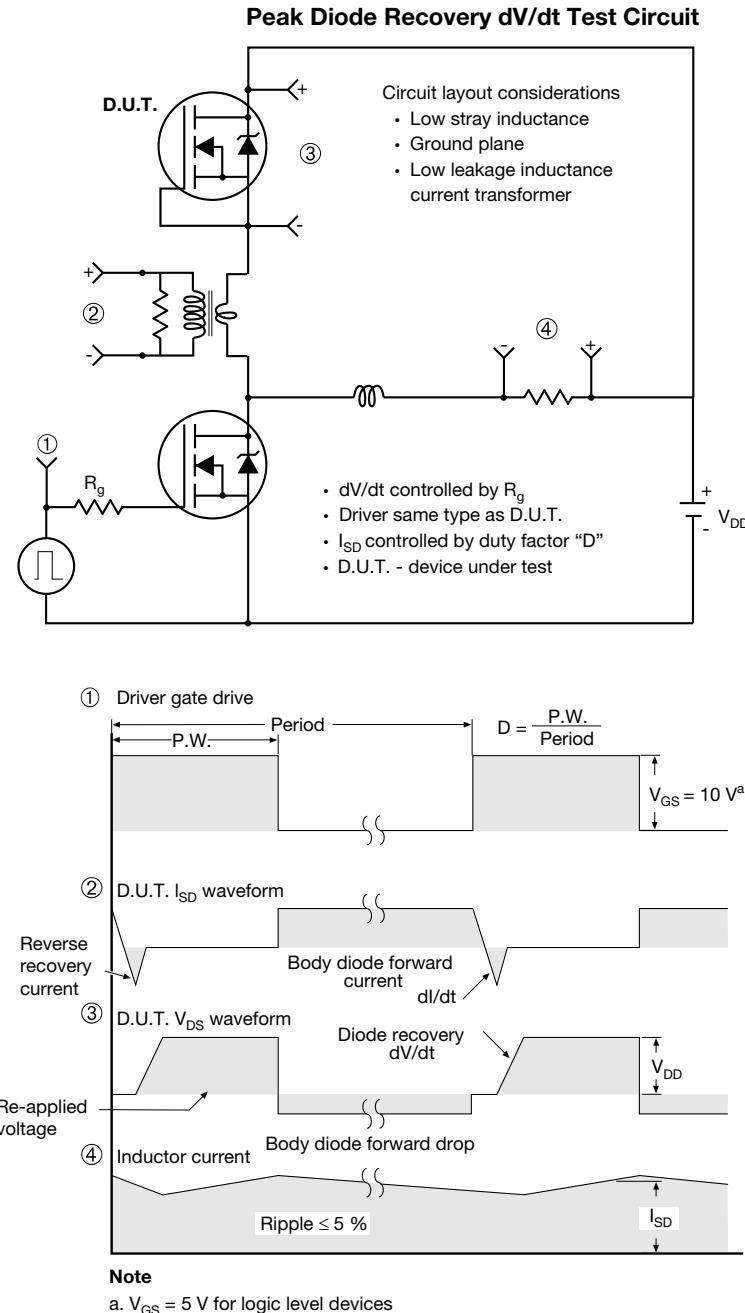
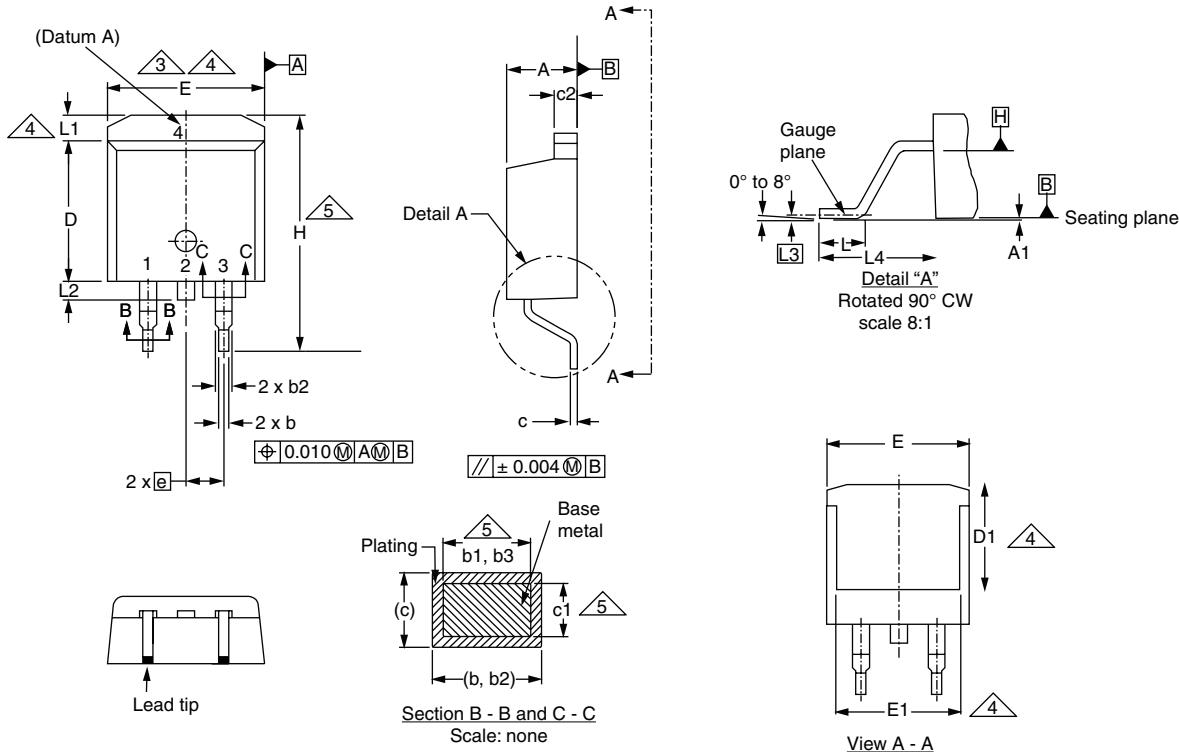


Fig. 14 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

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